

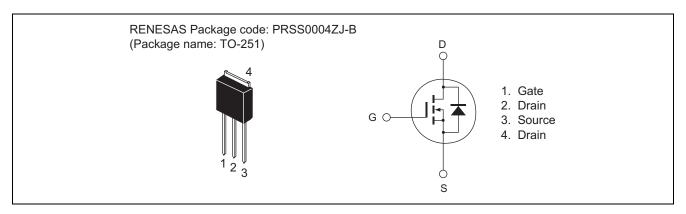
# RJK6025DPH-E0

600V - 1A - MOS FET High Speed Power Switching R07DS1012EJ0100 Rev.1.00 Feb 12, 2013

#### **Features**

- Low on-resistance  $R_{DS(on)}=13~\Omega~typ.~(at~I_D=0.5~A,~V_{GS}=10~V,~Ta=25^{\circ}C)$
- Low drive current
- High density mounting

#### **Outline**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	600	V
Gate to source voltage	$V_{GSS}$	±30	V
Drain current	I <sub>D</sub>	1	А
Drain peak current	I <sub>D (pulse)</sub> Note1	2	А
Body-drain diode reverse drain current	I <sub>DR</sub>	1	А
Body-drain diode reverse drain peak current	I <sub>DR</sub> (pulse)	2	А
Channel dissipation	Pch Note2	29.7	W
Channel to case thermal impedance	θch-c	4.2	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value at Tc = 25°C

## **Electrical Characteristics**

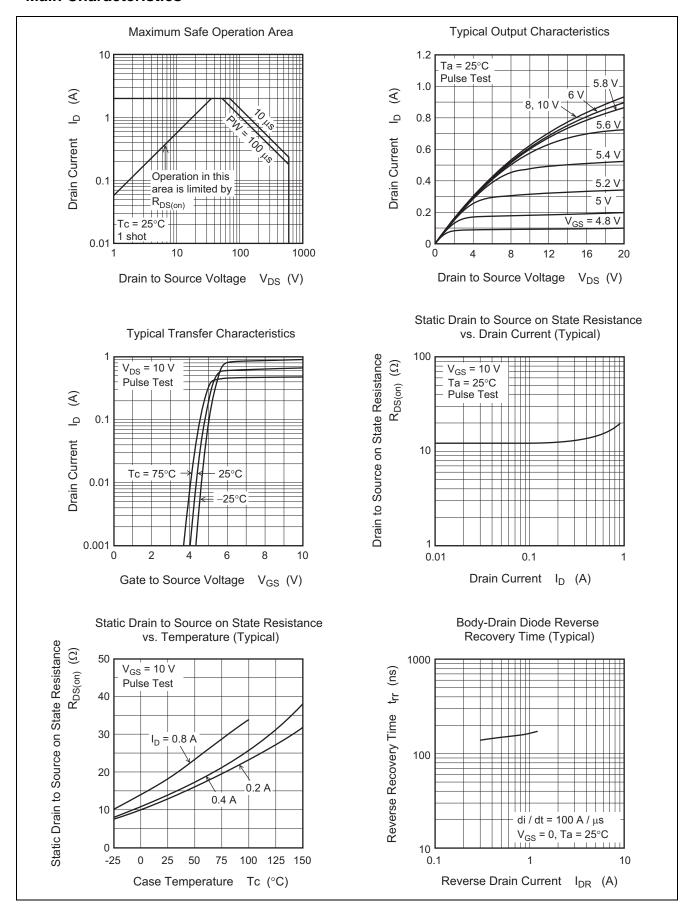
 $(Ta = 25^{\circ}C)$ 

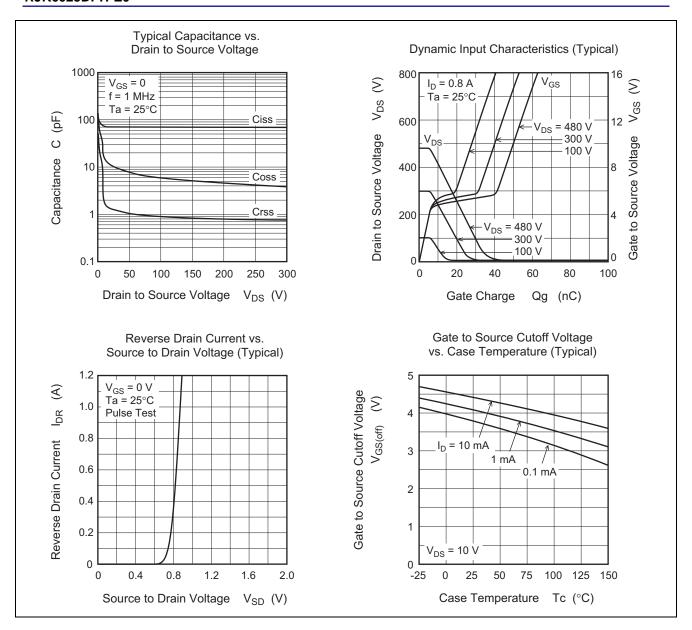
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600		_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>			1	μΑ	$V_{DS} = 600 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>		_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3	_	5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R <sub>DS(on)</sub>	_	13.5	17.5	Ω	$I_D = 0.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note3}}$
Input capacitance	Ciss		37.5	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	7.5	_	pF	V <sub>GS</sub> = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	0.9	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	30	_	ns	$I_D = 0.2 \text{ A}$ $V_{GS} = 10 \text{ V}$ $R_L = 1500 \Omega$ $Rg = 10 \Omega$
Rise time	t <sub>r</sub>	_	14.5	_	ns	
Turn-off delay time	$t_{d(off)}$	_	48	_	ns	
Fall time	t <sub>f</sub>	_	77	_	ns	
Total gate charge	Qg	_	5.0	_	nC	$V_{DD} = 480 \text{ V}$ $V_{GS} = 10 \text{ V}$ $I_D = 1.0 \text{ A}$
Gate to source charge	Qgs	_	0.7	_	nC	
Gate to drain charge	Qgd	_	3.3	_	nC	
Body-drain diode forward voltage	$V_{DF}$	_	0.85	1.45	V	$I_F = 1.0 \text{ A}, V_{GS} = 0^{\text{Note3}}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	230	_	ns	$I_F = 0.4 \text{ A}, V_{GS} = 0$ di <sub>F</sub> /dt = 100 A/ $\mu$ s

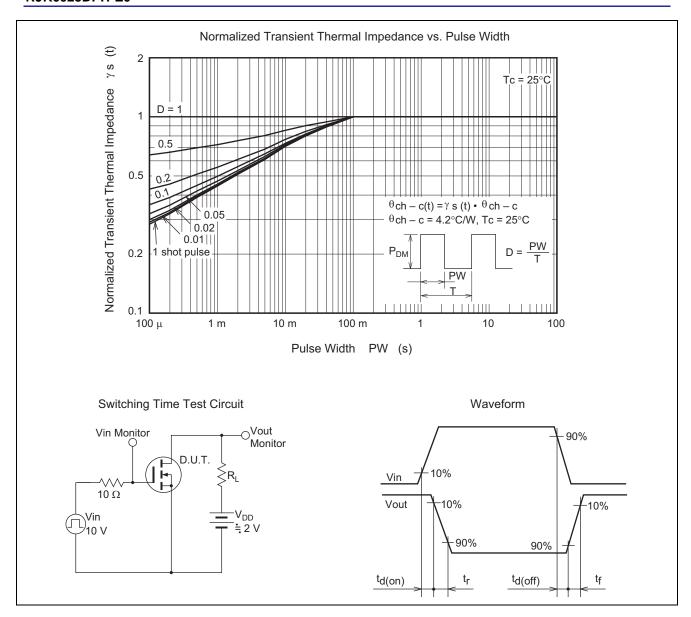
Notes: 3. Pulse test

- 4. Since this device is equipped with high voltage FET chip ( $V_{DSS} \ge 600 \text{ V}$ ), high voltage may be supplied. Therefore, please be sure to confirm about Electric discharge between Drain terminal and other terminal.
- This device is sensitive to electrostatic discharge.
   It is recommended to adopt appropriate cautions when handling this product.

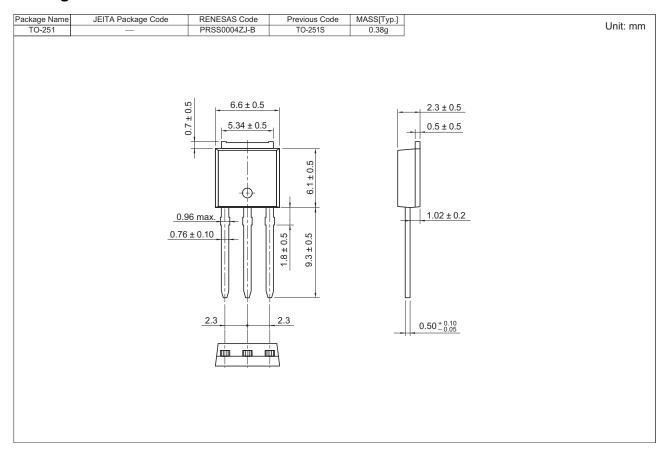
### **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

Orderable Part No.	Quantity	Shipping Container
RJK6025DPH-E0#T2	70 pcs	Tube

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